



## TO-92S Plastic-Encapsulate Transistors

### 2SC2389S TRANSISTOR (NPN)

#### FEATURES

- High Breakdown Voltage.
- Complements the 2SA1038S.

#### TO - 92S

1. EMITTER
2. COLLECTOR
3. BASE



#### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	120	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current	50	mA
$P_C$	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	417	$^\circ\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^\circ\text{C}$

#### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}, I_E=0$	120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=100\text{V}, I_E=0$			0.5	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4\text{V}, I_C=0$			0.5	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=6\text{V}, I_C=2\text{mA}$	180		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.5	V
Collector output capacitance	$C_{ob}$	$V_{CB}=12\text{V}, I_E=0, f=1\text{MHz}$		2.5		pF
Transition frequency	$f_T$	$V_{CE}=12\text{V}, I_C=2\text{mA}, f=100\text{MHz}$		140		MHz

#### CLASSIFICATION OF $h_{FE}$

RANK	R	S
RANGE	180-390	270-560